



PLD850-2-T

Features

- MOCVD Pulsed Laser Diode
- Wavelength : 850 nm (Typ.)
- Peak Power : 2W
- Threshold Current : 100 mA (Typ.)
- Package Style : TO-18 (5.6 mmØ)

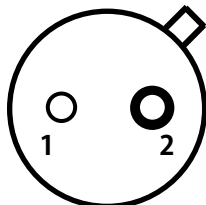
TEMPERATURE CHARACTERISTICS

DESCRIPTION	SYMBOL	RATED VALUE
Operation Temperature (°C)	T _{op}	-30 to +70
Storage Temperature (°C)	T _{stg}	-60 to +85

OPTICAL AND ELECTRICAL CHARACTERISTICS (Tc=25 °C); Test condition: 50ns, 1kHz

DESCRIPTION	SYMBOL	MIN.	TYPICAL	MAX.
Lasing Wavelength (nm)	λ_p	835	850	865
Emitting Area	Ae	-	40 x 1 um	-
Peak Power (W)	Po	-	-	5
Threshold Current (mA)	I _{th}	80	100	120
Peak Current (A)	I _{op}	-	-	2
Peak Voltage (V)	Vop	-	-	6
Beam Divergence (°)	$\theta_{ }$	-	10	-
Beam Divergence ⊥ (°)	θ_{\perp}	-	30	-
Duty Factor (%)	DF	***	0.1	***

Pin Layout:



bottom view

Pin1 = LD Cathode

Pin2 = LD Anode